

MOSFET

-116 A , -30V , 4.3mΩ P-CHANNEL MOSFET

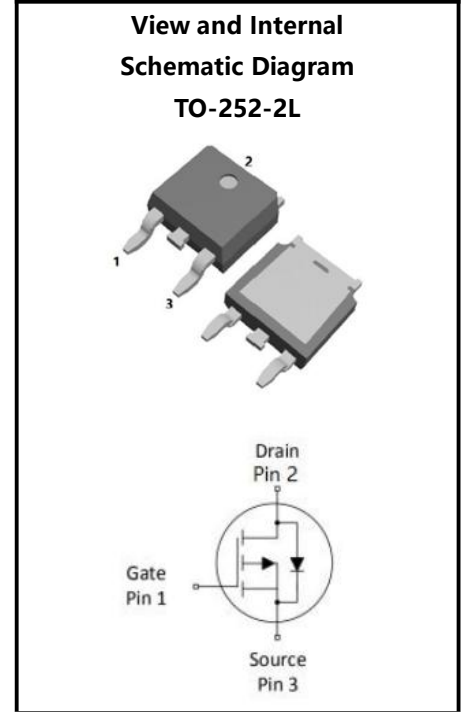
Features

- ◆ Low gate charge
- ◆ 100% UIS Tested, 100% DVDS Tested
- ◆ High Power and current handing capability
- ◆ Lead free product is acquired

Applications

- ◆ DC/DC Converter
- ◆ Ideal for high-frequency switching and synchronous rectification

Parameter	Values	Unit
BV_{DSS}	-30	V
I_D	-116	A
$R_{Dson}(max)$	4.3	mΩ
$V_{GS(th)}(Typ)$	-1.7	V



Ordering Code	Marking	Package	Packaging
X4P3P030TLE2	X4P3P030TLE2	TO-252-2L	Tape and reel

Absolute Maximum Ratings($T_C=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Drain-Source Voltage	V_{DSS}	-	-	-30	V	-
Gate-Source Voltage	V_{GS}	-20	-	20	V	-
Continuous Drain Current(Note 1)	I_D	-	-	-116	A	$T_C=25^{\circ}C$
		-	-	-81	A	$T_C=100^{\circ}C$
Pulsed Drain Current(Note 2)	I_{DM}	-	-	-464	A	
Single Pulse Avalanche Energy	E_{AS}	-	-	576	mJ	$L=0.5mH, V_D=-30V, T_C=25^{\circ}C$
Maximum Power Dissipation	P_D	-	-	107	W	$T_C=25^{\circ}C$
		-	-	53	W	$T_C=100^{\circ}C$
Operating Junction and Storage Temperature Range	T_{j}, T_{STG}	-55	-	175	$^{\circ}C$	-

Thermal Characteristics

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Thermal resistance , Junction to Case	$R_{th(j-c)}$	-	1.4	-	$^{\circ}C/W$	-

Electrical Characteristics ($T_j=25^{\circ}\text{C}$, unless otherwise noted)

Static characteristics

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Drain-Source Breakdown Voltage	BV_{DSS}	-30	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1	μA	$V_{DS}=-30V, V_{GS}=0V$
Gate-Body Leakage Current, Forward	I_{GSSF}	-	-	100	nA	$V_{GS}=20V, V_{DS}=0V$
Gate-Body Leakage Current, Reverse	I_{GSSR}	-	-	-100	nA	$V_{GS}=-20V, V_{DS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0	-	-2.5	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Drain-Source On-State Resistance	$R_{DS(on)}$	-	3.6	4.3	m Ω	$V_{GS}=-10V, I_D=-20A$
		-	5.4	7	m Ω	$V_{GS}=-4.5V, I_D=-20A$
Gate Resistance	R_g	-	2.2	-	Ω	$V_{GS}=0V, V_{DS}=0V, f=1\text{MHz}$
Forward Transconductance	g_{fs}	-	60	-	S	$V_{DS}=-5V, I_D=-20A$

Dynamic characteristics

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Input Capacitance	C_{iss}	-	7000	-	pF	$V_{DS}=-15V, V_{GS}=0V, f=1.0\text{MHz}$
Output Capacitance	C_{oss}	-	820	-		
Reverse Transfer Capacitance	C_{rss}	-	540	-		
Turn-On Delay Time	$t_{d(on)}$	-	13	-	ns	$V_{DD}=-15V, R_G=3\Omega, V_{GS}=-10V, R_L=0.75\Omega$
Turn-On Rise Time	t_r	-	32	-		
Turn-Off Delay Time	$t_{d(off)}$	-	27	-		
Turn-Off Fall Time	t_f	-	9	-		

Gate charge characteristics

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Total Gate Charge	Q_g	-	14.2	-	nC	$V_{DS}=-15V, I_D=-20A, V_{GS}=-10V$
Gate-Source Charge	Q_{gs}	-	1.1	-		
Gate-Drain Charge	Q_{gd}	-	4.8	-		

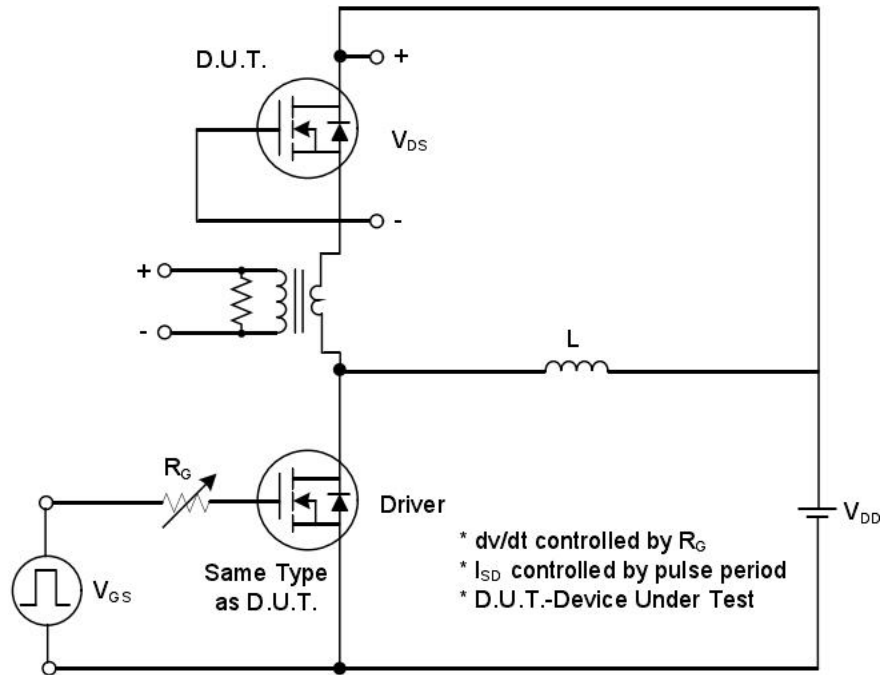
Reverse diode

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Continuous Diode Forward Current	I_{SD}	-	-	-112	A	-
Diode Forward Voltage (Note 3)	V_{SD}	-	-	-1.2	V	$I_S=-20A, V_{GS}=0V$
Reverse Recovery Time	t_{rr}	-	30	-	ns	$V_{GS}=0V, I_S=-20A, di/dt=100A/\mu s$
Reverse Recovery Charge	Q_{rr}	-	40	-	nC	

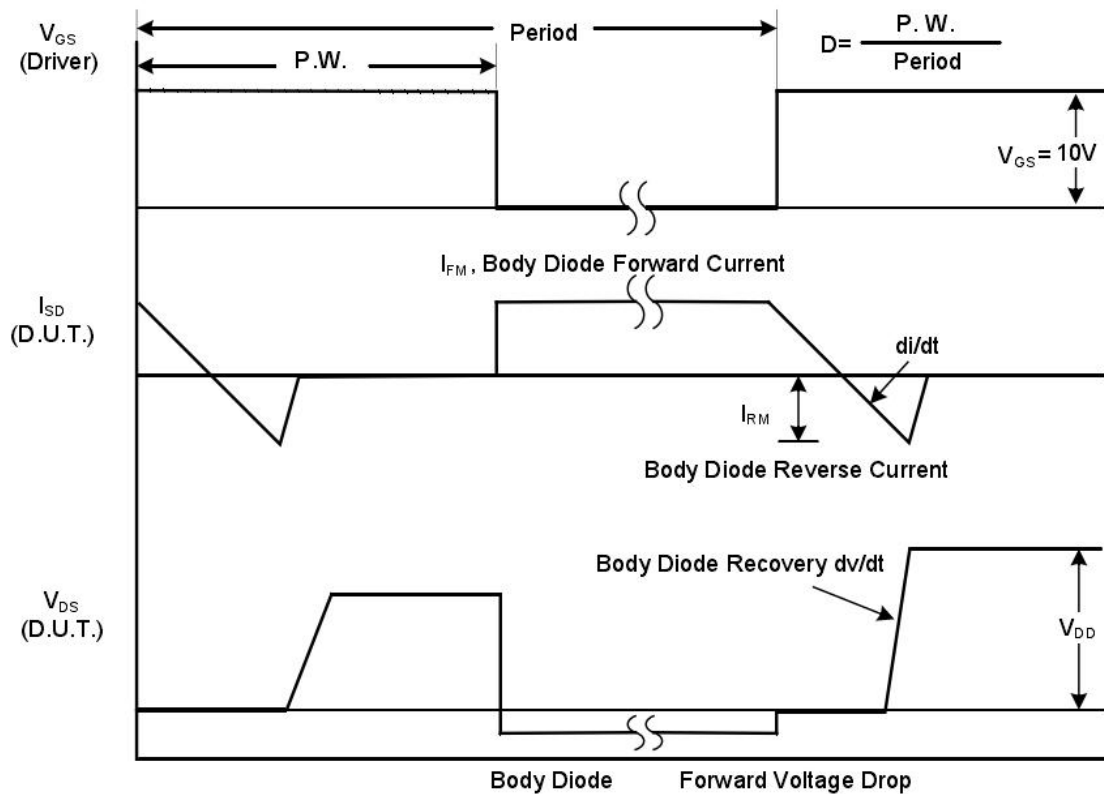
Notes

1. Computed continuous current assumes the condition of T_{j_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{j_Max} = 150^{\circ}\text{C}$.

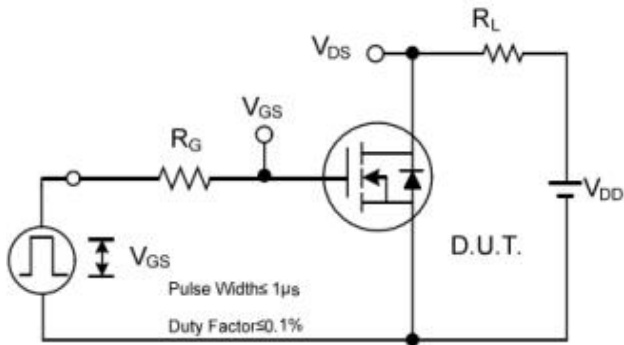
RATING AND CHARACTERISTIC CURVES



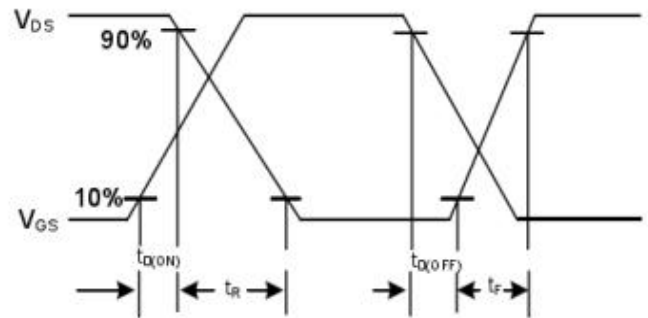
Peak Diode Recovery dv/dt Test Circuit



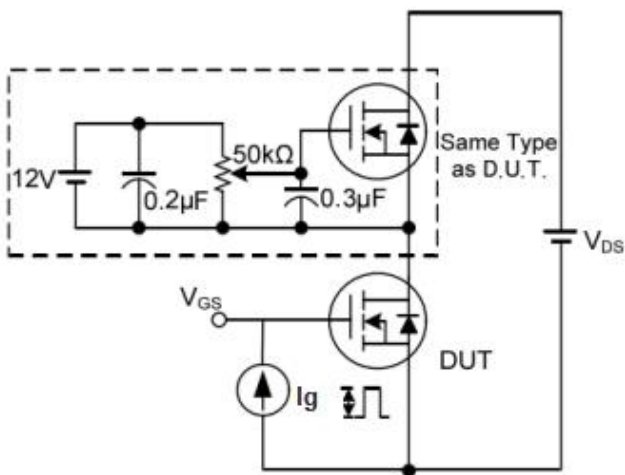
Peak Diode Recovery dv/dt Waveforms



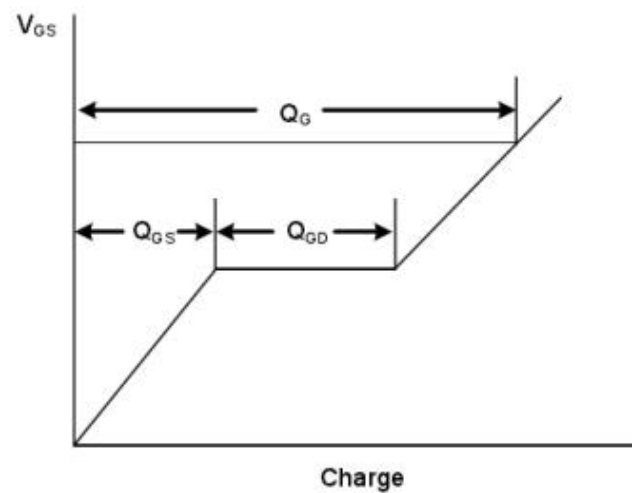
Switching Test Circuit



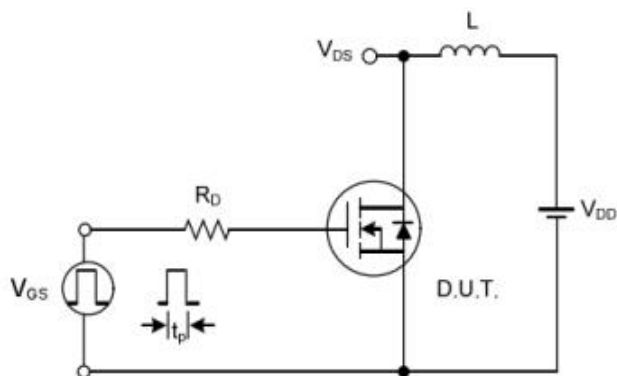
Switching Waveforms



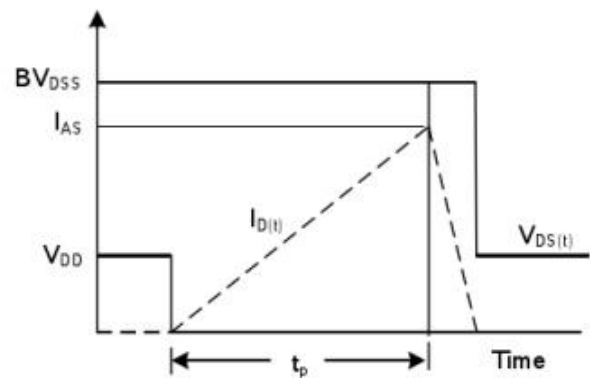
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

RATING AND CHARACTERISTIC CURVES

Figure.1 Output Characteristics

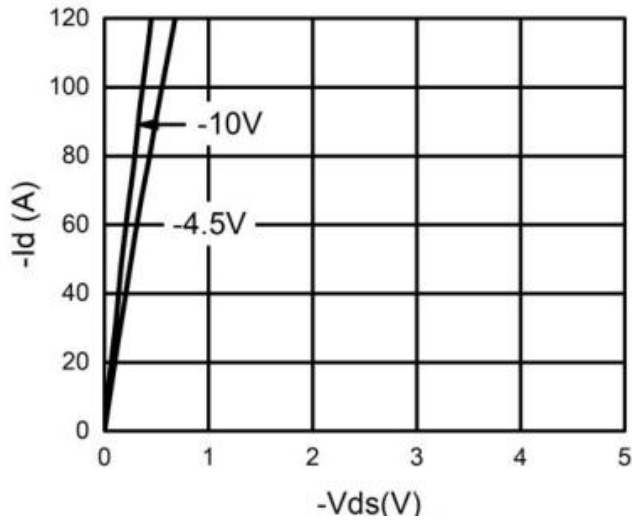


Figure.2 Transfer Characteristics

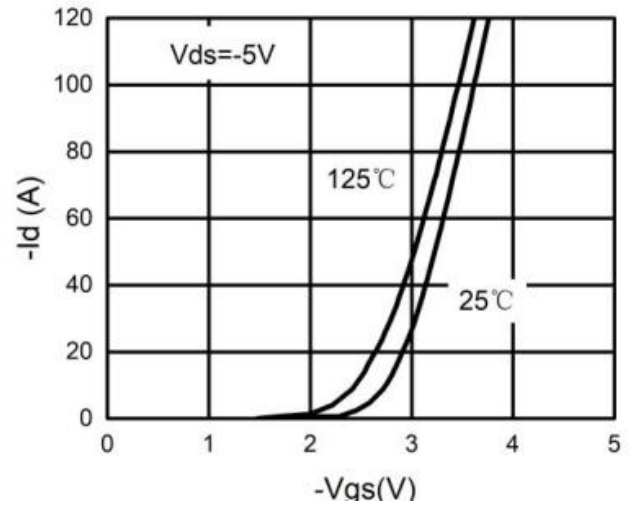


Figure.3 Power Dissipation

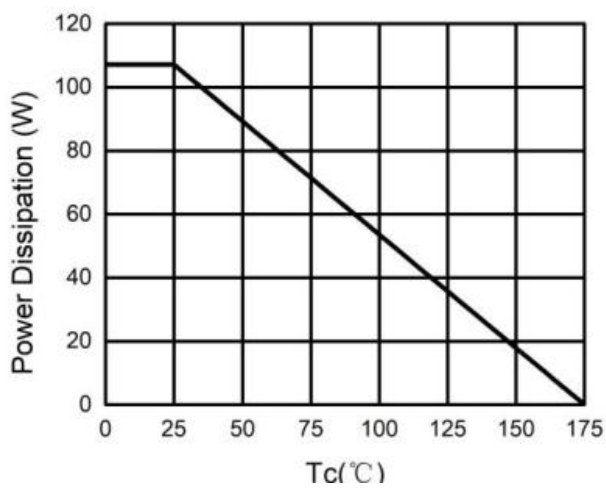


Figure.4 Drain Current

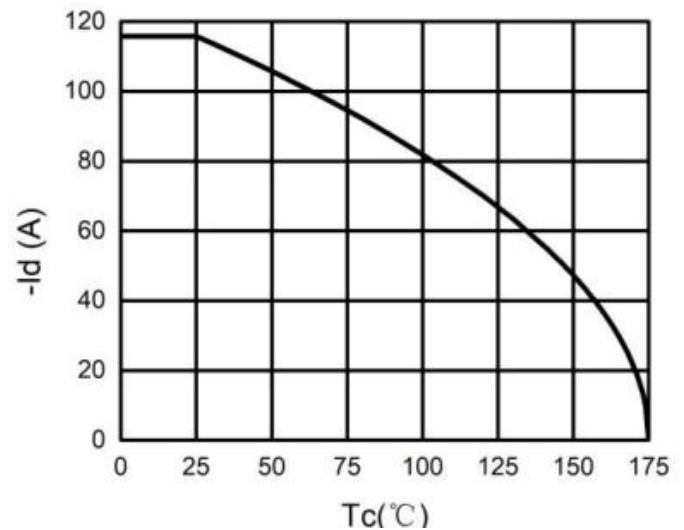


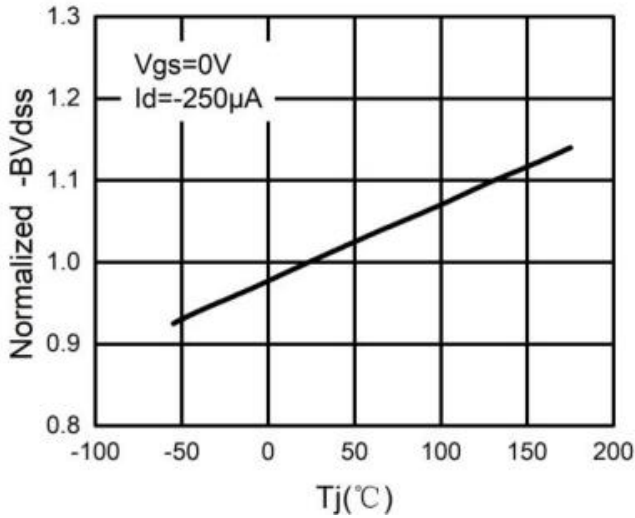
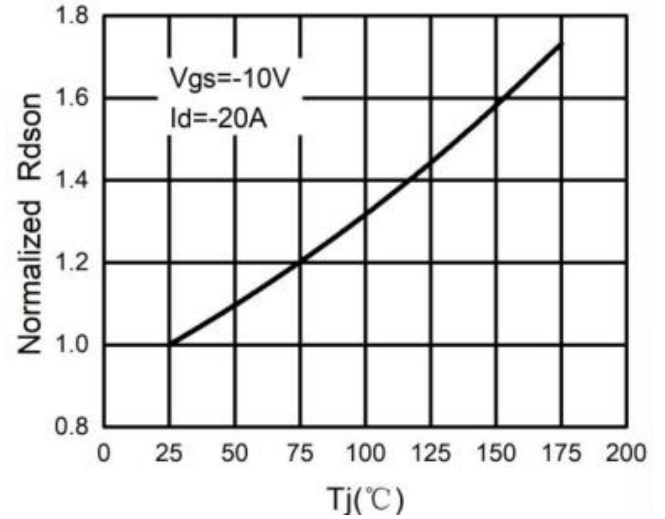
Figure.5 BV_{DSS} vs Junction Temperature

Figure.6 $R_{DS(ON)}$ vs Junction Temperature


Figure.7 Gate Charge Waveforms

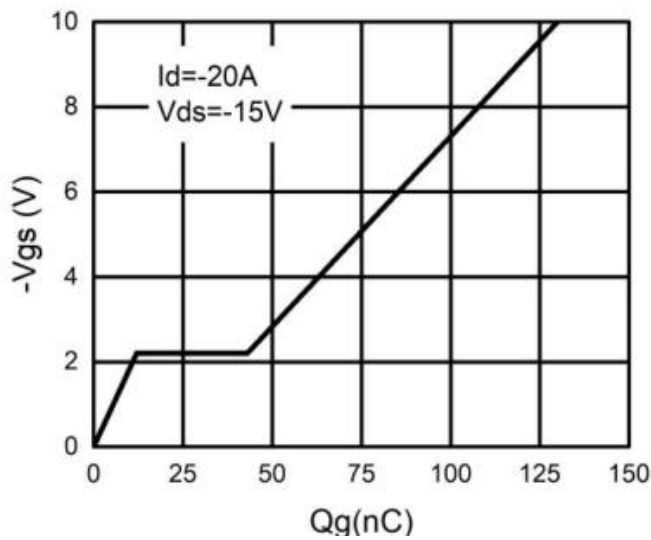


Figure.8 Capacitance

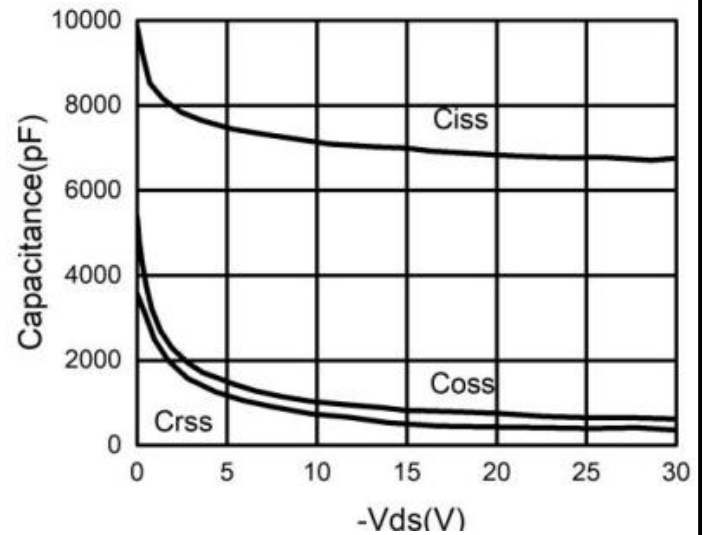


Figure.9 Body-Diode Characteristics

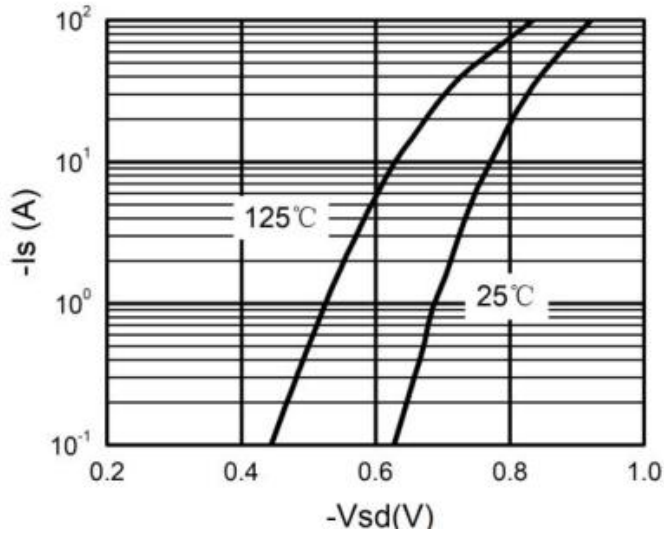
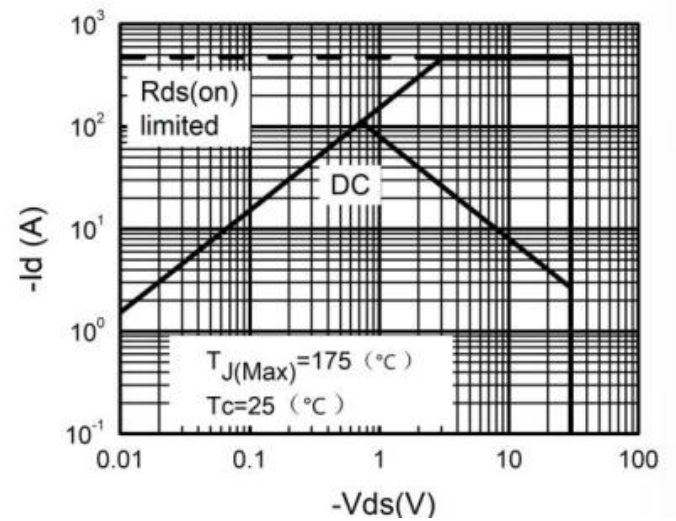
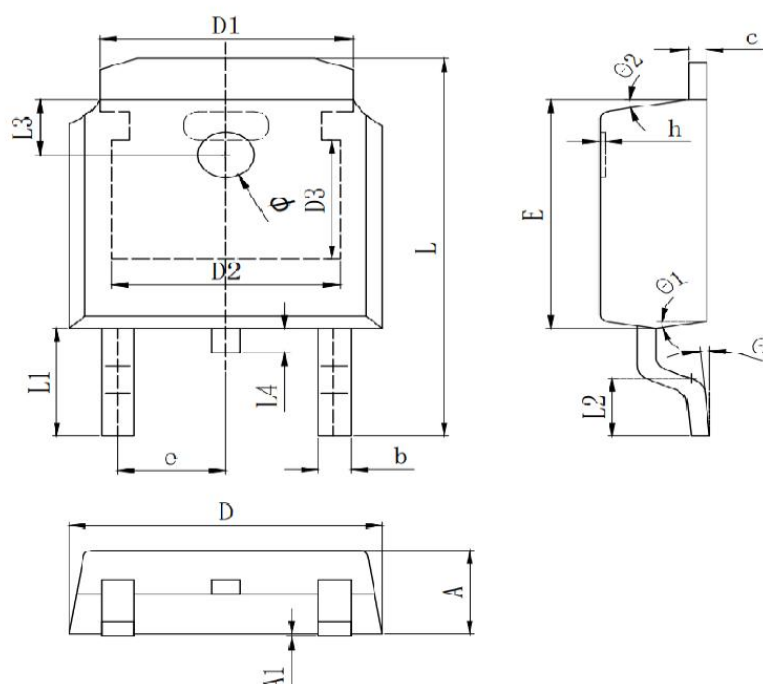


Figure.10 Maximum Safe Operating Area



Package Outline: TO-252-2L



Symbol	Dimensions In Millimeters		
	Min	Typ	Max
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334REF		
D2	4.826REF		
D3	3.166REF		
E	6.000	6.100	6.200
e	2.286TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888REF		
L2	1.400	1.550	1.700
L3	1.600REF		
L4	0.600	0.800	1.000
Φ	1.100	1.200	1.300
θ	0°		8°
θ1	9° TYP		
θ2	9° TYP		